Debo Ajagunna

Adebowale Olufunso (Debo) Ajagunna - Brief Biography

Adebowale Olufunso (Debo) Ajagunna, a native of Nigeria moved to Greece and obtained his PhD in Physics from the University of Crete in 2011. His thesis was entitled "Heteroepitaxy of InN on silicon (111) and R-Plane sapphire substrates" and it was performed under the supervision of Prof. Alexandros Georgakilas. At the time he also served a church in Heraklion. The church is composed of expatriate converts, many of them from Nigeria. After his PhD Debo return back to Nigeria, to be with his wife and three children. On May 1, 2012 he was praying with members of his former congregation in Ikare-Akoko, a city in the southwestern Nigerian state of Ondo, when armed robbers entered the church building. "Everyone ran for their life," said Eleni Melirrytos, a member of the Omonia Church of Christ in Athens, Greece, and longtime friend of Ajagunna. "There was a pregnant lady who got shot and was asking for help. Debo had already left the room but came back to help her. That is when he got shot." Ajagunna died from his injuries. The pregnant woman (and her unborn child) survived the attack.

Publications

1. "Angular-dependent Raman study of a- and s-plane InN"

2. "Extraction of absorption coefficients from as-grown GaN nanowires on opaque substrates using all-optical method"
R. Jayaprakash, D. Ajagunna, S. Germanis, M. Androulidaki, K. Tsagaraki, A. Georgakilas and N. T. Pelekanos
Optics Express 22, 19555 (2014)

3. "Self-annihilation of inversion domains by high energy defects in III-Nitrides"
T. Koukoula, J. Kioseoglou, Th. Kehagias, A. O. Ajagunna, Ph. Komninou and A. Georgakilas

4. "Growth mechanism and microstructure of low defect density InN (0001) In-face thin films on Si (111) substrates"

5. "Structural characteristics of single crystalline GaN films grown on (111) diamond with AlN buffer"
B. Pécz, L. Tóth, Á. Barna, G. Tsiakatouras, A. O. Ajagunna, A. Kovács and A. Georgakilas
Diamond & Related Materials 34, pp. 9-12 (2013)
6. “Optical characterization of free electron concentration in heteroepitaxial InN layers using Fourier transform infrared spectroscopy and a 2×2 transfer-matrix algebra”
C. C. Katsidis, A. O. Ajagunna and A. Georgakilas
J. Appl. Phys. 113, 073502 (2013)
7. “Structure and interfacial properties of semipolar s-plane (1-101) InN grown on r-plane sapphire”
G. P. Dimitrakopulos, A. Lotsari, Th. Kehagias, A. Ajagunna and A. Georgakilas, Th. Karakostas and Ph. Komninou
8. “Structural characterization of InN epilayers grown on r-plane sapphire by plasma-assisted MBE”
9. “Influence of high electron concentration on band gap and effective electron mass of InN”
Phys. St. Sol. (b) 248, pp. 1172-1175 (2011)
10. “Longitudinal polar optical phonons in InN/GaN single and double heterostructures”
S. Ardali, E. Tiras, M. Gunes, N. Balkan, A. O. Ajagunna, E. Iliopoulos and A. Georgakilas
Phys. St. Sol. (c) 7, pp. 1620-1624 (2011)
11. “Microstructure of N-face InN grown on Si (111) by plasma-assisted MBE using a thin GaN-AlN buffer layer”
G. P. Dimitrakopulos, Th. Kehagias, A. Ajagunna, J. Kioseoglou, I. Kerasiotis, G. Nouet, A. P. Vajpeyi, Ph. Komninou and Th. Karakostas
12. “Epitaxial growth, electrical and optical properties of a-plane InN on r-plane sapphire”
A. O. Ajagunna, E. Iliopoulos, G. Tsiakatouras, K. Tsagaraki, M. Androulidaki and A. Georgakilas
J. Appl. Phys. 107, 024506 (2010)
13. “InGaN nanopillars grown on silicon substrate using plasma assisted molecular beam epitaxy”
A. P. Vajpeyi, A. O. Ajagunna, K. Tsagaraki, M. Androulidaki and A. Georgakilas,
Nanotechnology 20, 325605 (2009)
14. “Spontaneous growth of III-nitride nanowires on Si by molecular beam epitaxy”
A. P. Vajpeyi, A. O. Ajagunna, G. Tsiakatouras, A. Adikimenakis, E. Iliopoulos, K. Tsagaraki, M. Androulidaki, and A. Georgakilas
15. “InN films and nanostructures grown on Si (111) by RF-MBE”
A. O. Ajagunna, A. Adikimenakis, E. Iliopoulos, K. Tsagaraki, M. Androulidaki, and A. Georgakilas

Source URL: https://www.physics.uoc.gr/el/node/1439

Links: